

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 59 (currently amended): A semiconductor light emitting device comprising a base having first and second external terminals, a semiconductor light emitting element secured to said base, and a light-permeable coating material for covering said semiconductor light emitting element, said semiconductor light emitting element comprising electrodes electrically connected respectively to said first and second external terminals,

wherein said coating material is selected from one of the following:

- (1) a glass of a polymetaloxane formed mainly based on the metaloxane bond from a metal alcooxide,
- (2) a gel of a polymetaloxane formed from a metal alcooxide, and
- (3) a ceramic formed from a polysilazane as a ceramic precursor; and said coating material tightly and strongly adheres directly to the semiconductor light emitting element and electrodes.

Claim 60 (cancelled):

Claim 61 (previously presented): A semiconductor light emitting device of claim 60, wherein said metal alcooxide is of one or more type selected from a single-metal alcooxide, a two-metal alcooxide and a multi-metal alcooxide.

Claim 62 (cancelled):

Claim 63 (previously presented): A semiconductor light emitting device of claim 62, wherein ceramic of said coating material is formed by applying a heat treatment to the ceramic precursor.

Claim 64 (previously presented): A semiconductor light emitting device of claim 59, wherein said coating material covers all the surfaces of said semiconductor light emitting element excluding the bottom surface thereof.

Claim 65 (previously presented): A semiconductor light emitting device of claim 59, wherein said base has a concavity filled with said coating material.

Claim 66 (previously presented): A semiconductor light emitting device of claim 59, wherein said base is an insulative substrate or a lead frame.

Claim 67 (previously presented): A semiconductor light emitting device of claim 59, wherein said semiconductor light emitting element emits light at light wavelengths of 365 nm to 550 nm.

Claim 68 (previously presented): A semiconductor light emitting device of claim 67, wherein said semiconductor light emitting element comprises a gallium nitride compound semiconductor light emitting element.

Claim 69 (cancelled):

Claim 70 (cancelled):

Claim 71 (previously presented): A semiconductor light emitting device of claim 59, wherein said coating material contains a fluorescent substance for receiving at least a part of the light projected from said semiconductor light emitting element to perform wavelength-conversion of the light.

Claim 72 (previously presented): A semiconductor light emitting device of claim 71, wherein said fluorescent substance absorbs at least a part of the light projected from said semiconductor light emitting element, and emits light having a wavelength longer than that of the light projected.

Claim 73 (previously presented): A semiconductor light emitting device of claim 72, wherein the light projected from said semiconductor light emitting element is mixed with the light wavelength-converted by said fluorescent substance to release the mixed light out of said coating material.

Claim 74 (previously presented): A semiconductor light emitting device of claim 59, wherein said coating material is covered with an encapsulant.

Claim 75 (previously presented): A semiconductor light emitting device of claim 74, wherein

said encapsulant is formed of a plastic which contains a light scattering material or a binder.

Claim 76 (previously presented): A semiconductor light emitting device of claim 75, wherein the light projected from said semiconductor light emitting element permeates said coating material before being released to the outside of said encapsulant.

Claim 77 (previously presented): A semiconductor light emitting device of claim 76, wherein said encapsulant is fitted into said concavity, and said coating material is formed between the bottom surface of said concavity and said encapsulant.

Claim 78 (previously presented): A semiconductor light emitting device of claim 59, wherein a concavity is formed in one principal surface of an insulative substrate for constituting said base; said semiconductor light emitting element is secured to the bottom surface of the concavity; and a pair of said electrodes in said semiconductor light emitting element is electrically connected to a pair of said external terminals formed on the one principal surface of said insulative substrate.

Claim 79 (previously presented): A semiconductor light emitting device of claim 59, wherein a lead frame for constituting said base has a pair of said external terminals; a concavity is formed in either of said external terminals; said semiconductor light emitting element is secured to the bottom surface of the concavity.

Claim 80 (new): A semiconductor light emitting device comprising a base having first and second external terminals, a semiconductor light emitting element secured to said base, and a

light-permeable coating material for covering said semiconductor light emitting element, said semiconductor light emitting element comprising electrodes electrically connected respectively to said first and second external terminals,

wherein said coating material is selected from one of the following:

- (1) a glass of a polymetaloxane formed mainly based on the metaloxane bond,
- (2) a gel of a polymetaloxane, and
- (3) a ceramic formed from a ceramic precursor, and

said coating material directly adheres to the semiconductor light emitting element and electrodes,

said semiconductor light emitting element is secured to said base by an adhesive of the same material as that of said coating material.